



95595SMC-02-1308

December 15, 2003

To: Commissioner for Patents
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Alexandria, VA 22313-1450

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Subject: | Serial No. 10/672,395 09/26/03 |

C.H. Yu et al.

METHOD OF SELECTIVELY MAKING COPPER
USING PLATING TECHNOLOGY

INFORMATION DISCLOSURE STATEMENT

Enclosed is Form PTO-1449, Information Disclosure Citation
In An Application.

The following Patents and/or Publications are submitted to
comply with the duty of disclosure under CFR 1.97-1.99 and
37 CFR 1.56.

CERTIFICATE OF MAILING

I hereby certify that this correspondence is being
deposited with the United States Postal Service as first class
mail in an envelope addressed to: Commissioner for Patents,
P.O. Box 1450, Alexandria, VA 22313-1450, on December 19, 2003.

Stephen B. Ackerman, Reg.# 37761

Signature/Date

U.S. Patent 6,420,258 to Chen et al., "Selective Growth of Copper for Advanced Metallization," describes a recent advance in copper deposition which involves a selective growth of copper by an electrochemical method on a conformal seed layer in a trench.

U.S. Patent 6,153,935 to Edelstein et al., "Dual Etch Stop/Diffusion Barrier for Damascene Interconnects," discloses a diffusion barrier cap selectively deposited on a metal interconnect which provides corrosion protection and improved electromigration resistance.

U.S. Patent 6,441,492 to Cunningham, "Diffusion Barriers for Copper Interconnect Systems," discusses a barrier layer which is rhenium, rhodium, or ruthenium formed on a copper interconnect and affords high resistance to Cu diffusion.

U.S. Patent 6,004,188 to Roy, "Method for Forming Copper Damascene Structures by Using a Dual CMP Barrier Layer," discloses an improved and new method for forming dual damascene CMP of copper lines and interconnects(studs) using a dual CMP barrier layer.

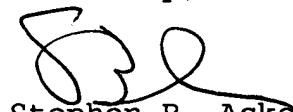
U.S. Patent 6,417,095 to Chen, "Method for Fabricating a Dual Damascene Structure," discusses a sacrificial layer used which eliminates the need for a CMP step.

U.S. Patent 6,528,426 to Olsen et al., "Integrated Circuit Interconnect and Method," discusses a SiC CMP stop layer utilized to protect an underlying mechanically weak dielectric layer such as porous SiO₂.

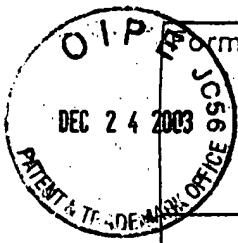
U.S. Patent 6,509,267 to Woo et al., "Method of Forming Low Resistance Barrier on Low K Interconnect with Electrolessly Plated Copper Seed Layer," discusses conformal nitride and Ta barrier layers being formed on the sidewalls of a dielectric layer to prevent Cu from being sputtered onto the dielectric layer during a via etch.

U.S. Patent 6,482,741 to Ueno, "Copper Wiring Structure Comprising a Copper Material Buried in a Hollow of an Insulating Film and a Carbon Layer Between the Hollow and the Copper Material in Semiconductor Device and Method Fabricating the Same," discusses a carbon electroconductive layer formed on the sidewalls and bottom of an opening in an amorphous C and F containing dielectric layer by a plasma treatment.

Sincerely,



Stephen B. Ackerman,
Reg. No. 37761



~~Form PTO-1449~~

INFORMATION DISCLOSURE CITATION IN AN APPLICATION

(Use several sheets if necessary)

Doctor's Name (Optional)

Afternoon Hours

TSMC-02-1308

10/672,395

Applicant S. H. Yu et al.

Ending Date: / / Original Act Date:

Filing Date 09/26/03

U. S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	MONO DATE IF APPROPRIATE
	64420258	7/16/02	Chen et al.	438	622	11/12/99
	6153935	11/28/00	Edelstein et al.	257	773	9/30/99
	6004188	12/21/99	Rey	451	41	9/10/98
	6417095	7/9/02	Chen	438	633	6/11/01
	6528426	3/4/03	Olsen et al.	438	689	10/15/99
	6509267	1/21/03	Woo et al.	438	687	6/20/01
	6482741	11/19/02	Ueno	438	687	8/20/99
	64414928	27/02	Cunningham	257	762	9/28/00

FOREIGN PATENT DOCUMENTS

	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO

OTHER DOCUMENTS (Including Author, Title, Date, Portion or Pages, Etc.)

EXAMINER

DATE CONSIDERED

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant.